In the Claims:

Please cancel claims 76-79 and 85-87.

Please amend claims 80-82 and 88-90 as follows:

1-79. (Cancelled)

~~80.~~ (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer in situ to a reducing environment;

depositing a second conductive layer; and

exposing the wafer to a material selected from the group consisting of phosphine, HCL, and boron trichloride, ~~The method of claim 76~~ wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

~~81.~~ (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer in situ to a reducing environment;

depositing a second conductive layer; and

exposing the wafer to a material selected from the group consisting of phosphine, HCL, and boron trichloride, ~~The method of claim 76~~ wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

~~82.~~ (Currently Amended) The method of claim ~~76~~ ~~80~~ further comprising forming a third conductive layer on the second conductive layer.

83. (Previously Added) The method of claim 82 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

84. (Previously Added) The method of claim 83 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

85-87. (Cancelled)

88. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer to a reducing environment;

depositing a second conductive layer; and

passivating at least one of the first and second conductive layers by exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride ~~The method of claim 85~~ wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

89. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer to a reducing environment;

depositing a second conductive layer; and

passivating at least one of the first and second conductive layers by exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride ~~The method of claim 85~~ wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

90. (Currently Amended) The method of claim ~~85~~ ~~88~~ further comprising forming a third conductive layer on the second conductive layer.

91. (Previously Added) The method of claim 90 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

92. (Previously Added) The method of claim 91 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

Please add new claims 93-110 as follows:

9 ~~93~~. (New) The method of claim 8 ~~81~~ further comprising forming a third conductive layer on the second conductive layer.

10 ~~94~~. (New) The method of claim 9 ~~93~~ further comprising forming a borophosphosilicate glass layer on the third conductive layer.

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11 ~~95~~. (New) The method of claim 10 ~~94~~ wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

12 ~~96~~. (New) The method of claim 8 ~~81~~ wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

13 ~~97~~. (New) The method of claim 8 ~~81~~ wherein exposing the wafer to a material selected from the group consisting of phosphine and boron trichloride comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

14 ~~98~~. (New) The method of claim 8 ~~81~~ wherein exposing the wafer to a material selected from the group consisting of phosphine HCL, and boron trichloride comprises exposing the wafer to this selection prior to depositing the second conductive layer.

5 ~~99~~. (New) The method of claim 1 ~~80~~ wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

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~~100~~ 6. (New) The method of claim ~~80~~ 1 wherein exposing the wafer to a material selected from the group consisting of phosphine and boron trichloride comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

~~101~~ 7. (New) The method of claim ~~80~~ 1 wherein exposing the wafer to a material selected from the group consisting of phosphine HCL, and boron trichloride comprises exposing the wafer to this selection prior to depositing the second conductive layer.

~~102~~ 23. (New) The method of claim ~~89~~ 22 further comprising forming a third conductive layer on the second conductive layer.

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~~103~~ 24. (New) The method of claim ~~102~~ 23 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

~~104~~ 25. (New) The method of claim ~~103~~ 24 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

~~105~~ 26. (New) The method of claim ~~89~~ 22 wherein exposing the wafer to a reducing environment comprises exposing the wafer to silane gas.

~~106~~ 27. (New) The method of claim ~~89~~ 22 wherein exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride comprises exposing the wafer to this selection prior to exposing the wafer to a reducing environment.

~~107~~ 28. (New) The method of claim ~~89~~ 22 wherein exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride comprises exposing the wafer to this selection prior to depositing the second conductive layer.

~~108~~ 19. (New) The method of claim ~~88~~ 15 wherein exposing the wafer to a reducing environment comprises exposing the wafer to silane gas.

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~~109~~. (New) The method of claim ~~88~~ wherein exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride comprises exposing the wafer to this selection prior to exposing the wafer to a reducing environment.

D3 cont.

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~~110~~. (New) The method of claim ~~88~~ wherein exposing the wafer to a material selected from the group consisting of diborane, phosphine, HCL, and boron trichloride comprises exposing the wafer to this selection prior to depositing the second conductive layer.

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